

# Monolithic Active Pixel Sensors for Charge Particle Tracking tests results

Yu.Gornushkin, G.Deptuch, W.Dulinski, D.Husson, J.L.Riester  
and M.Winter

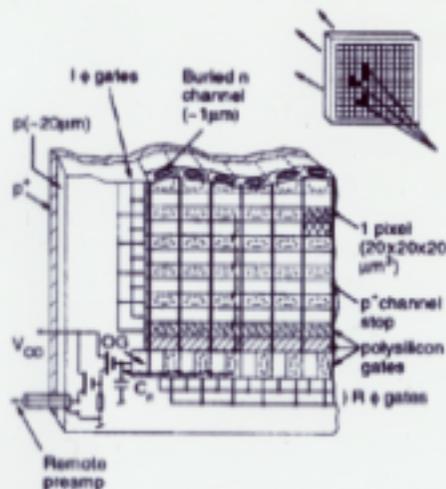
IREs and LEPSI, ULP/IN2P3, Strasbourg, France  
W.de Boer, J. Bol, A. Dierlamm, M. Koppenhoefer Univ. of Karlsruhe, Germany

## Contents

- Idea and basic architecture of a CMOS MAPS
- Prototype MIMOSA chip
- High energy particles beam test results :  
S/N, efficiency, charge distribution,  
spatial resolution
- Magnet test results
- Conclusion and Future Development Prospects

# PIXEL DETECTORS

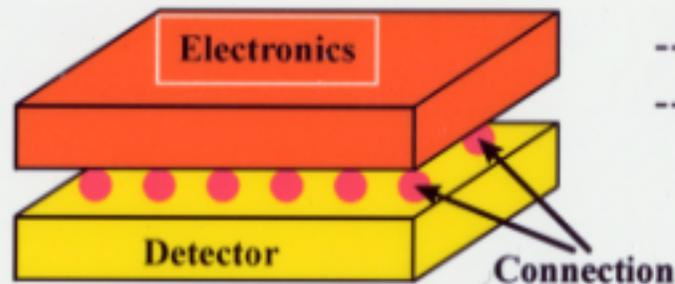
## CCD



- > Imaging
- > High Energy Physics (SLD)

## APS (Active Pixel Sensor)

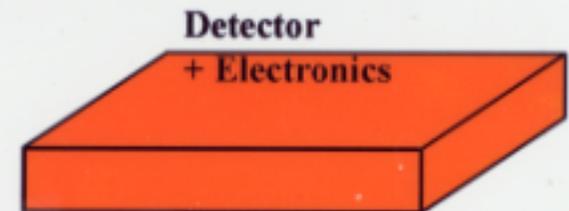
### hybride APS



- > High Energy Physics (DELPHI, ...)

### High Resistivity monolithic APS

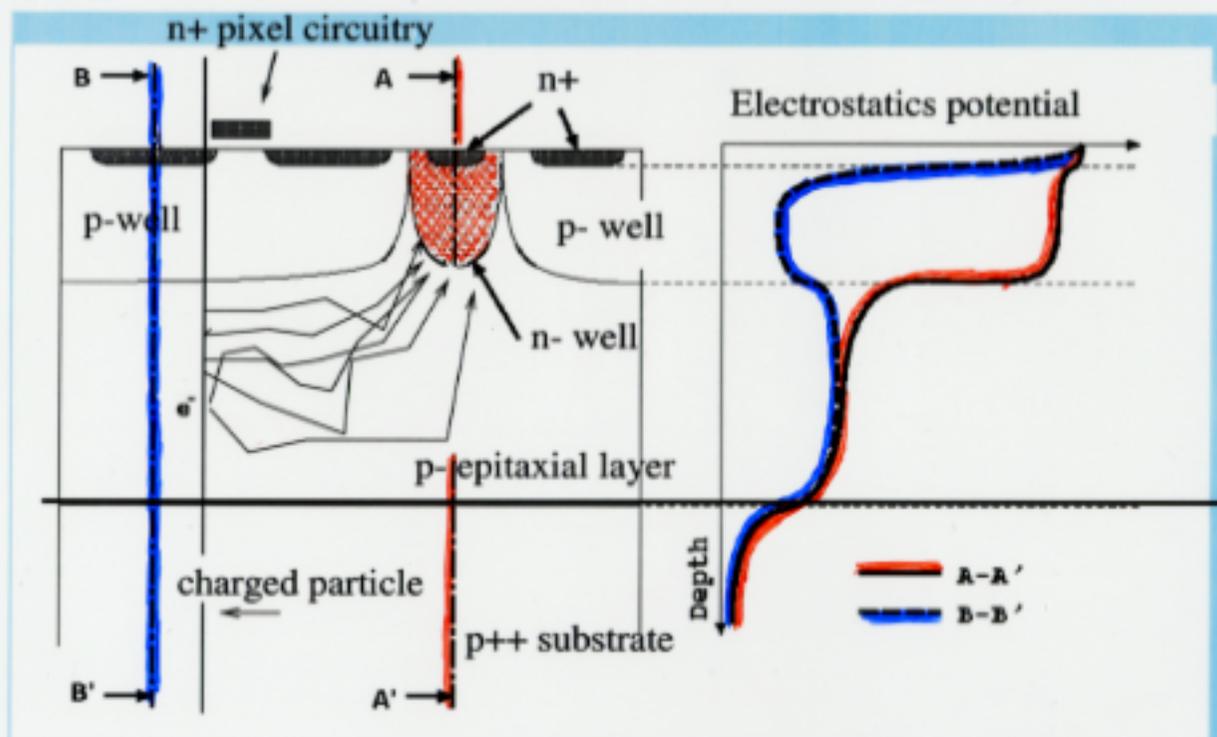
- > High Energy Physics
- > Complex technology



### Low Resistivity monolithic APS

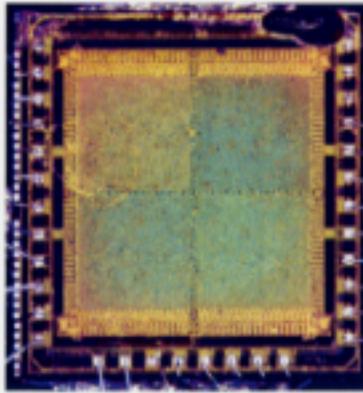
- > Imaging
- > Standard VLSI Technology

## Cross-section of a CMOS wafer with a charge collecting structure allowing 100% Fill Factor, essential for tracking application

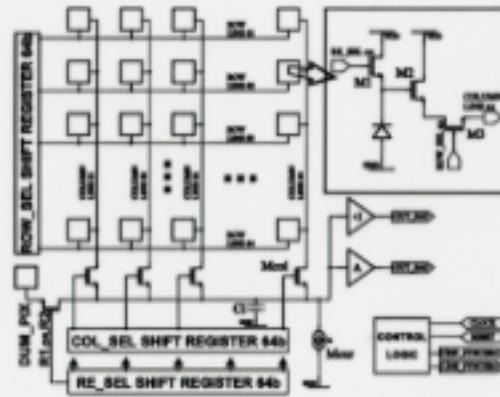


**Advantages of a standard (submicron) CMOS : availability, cost, radiation hardness, feasibility of a "system on a chip" solution**

## Mimosa I and Mimosa II single cell electronics and readout architecture



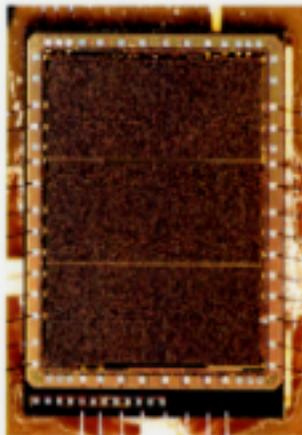
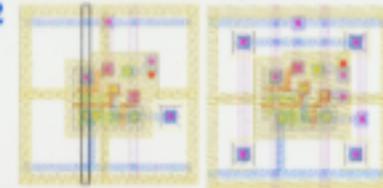
MIMOSA I die photo



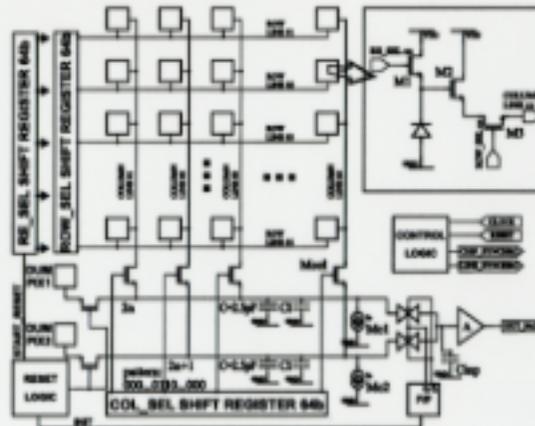
MIMOSA I block schematic diagram

- standard 0.6 $\mu$ m CMOS ( $t_{ox}=12.7$ nm)
- 14 $\mu$ m thick EPI layer ( $10^{14}$ cm $^{-3}$ )
- 4 arrays 64x64 pixels
- pixel pitch 20x20 $\mu$ m $^2$
- diode (nwell/p-epi) size 3x3 $\mu$ m $^2$  - 3.1fF
- serial analogue readout
- max. clock freq.: 5MHz
- die size 3.6x4.2mm $^2$
- technology 3M+2P
- power supply 5V

MIMOSA I  
pixels layouts



MIMOSA II die photo



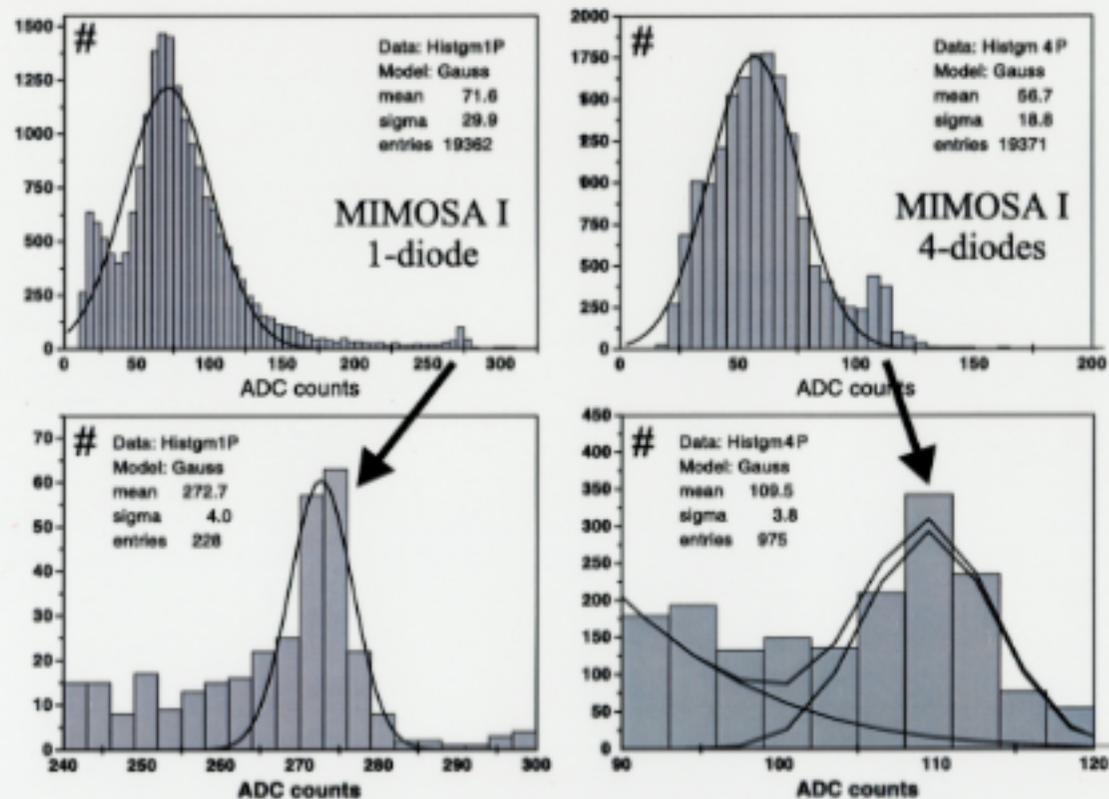
MIMOSA II block schematic diagram

- standard 0.35 $\mu$ m CMOS ( $t_{ox}=7.4$ nm)
- 4.2 $\mu$ m thick EPI layer ( $10^{15}$ cm $^{-3}$ )
- 6 arrays 64x64 pixels
- pixel pitch 20x20 $\mu$ m $^2$
- diode (nwell/p-epi) size 1.7x1.7 $\mu$ m $^2$  - 1.65fF
- serial analogue readout
- max. clock freq.: 25MHz
- die size 4.9x3.5mm $^2$
- technology 5M+2P
- power supply 3.3V
- radiation tolerant transistor design

MIMOSA II  
pixels layouts



## Gain calibration using soft X-rays (5.9 keV from $^{55}\text{Fe}$ )



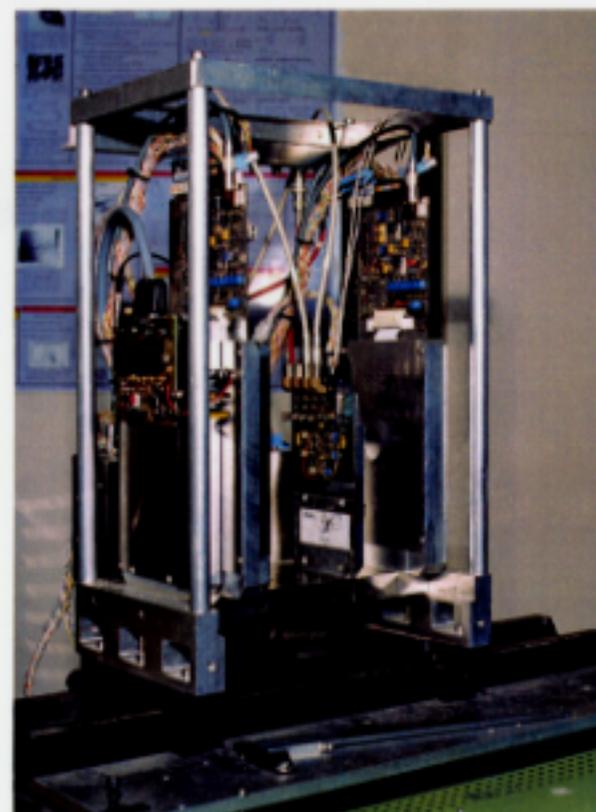
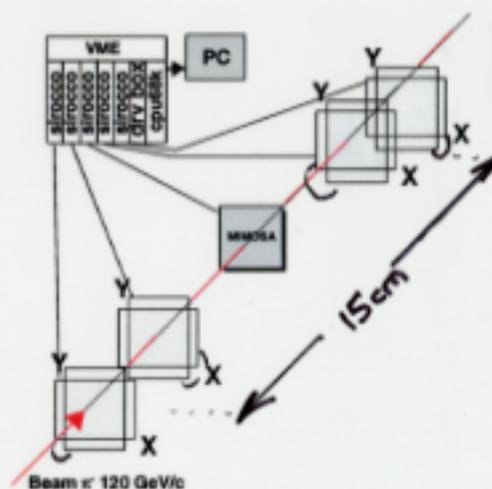
- The "big peak" doesn't correspond with 100% of charge collection
- Taking second peak position (conversion in a depletion region of the collecting diode)...

# Testbeam setup

@CERN SPS:  $\pi$  120 GeV/c  
Precise silicon strip beam  
telescope with 8 planes (X,Y)  
with resolution of  $\sim 2\mu\text{m}$

DAQ based on VME OS9

After the alignment,  
tracks reconstruction and  
selection...

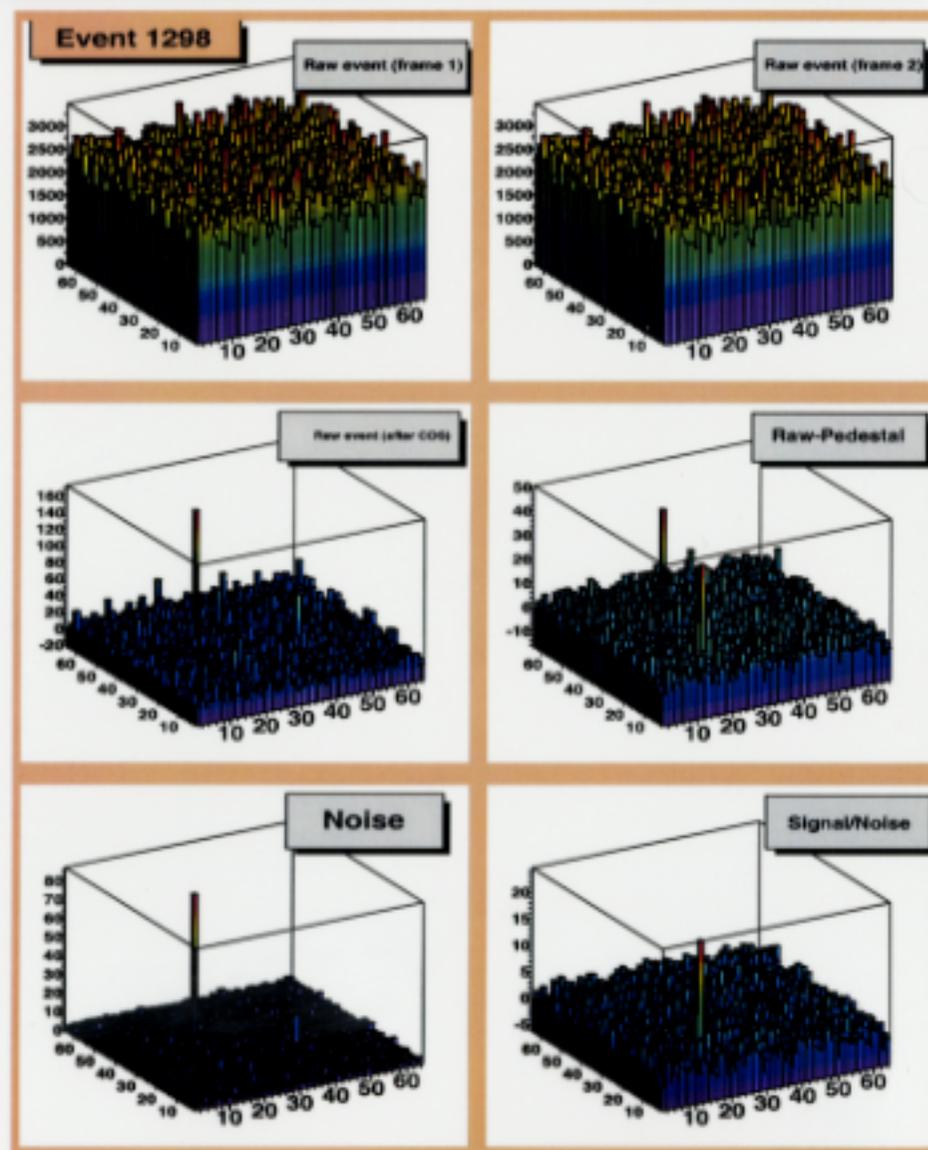


...the track position in the  
middle of the telescope was predicted  
with precision  $\sim 1\mu\text{m}$ .

# Signal processing

Off-line CDS processing to eliminate kTC noise, common mode, FPN...

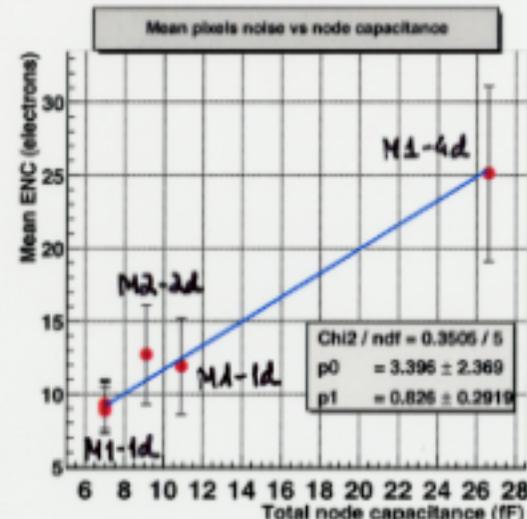
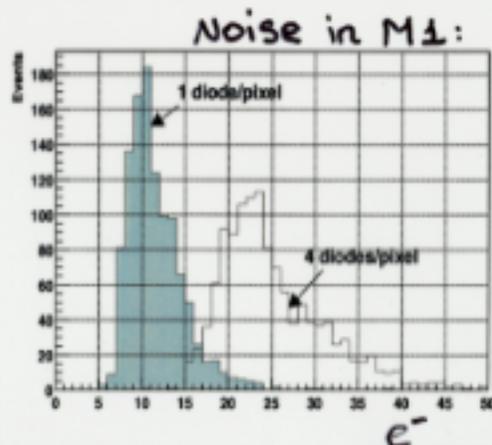
Remaining noise due to leakage current fluctuations measured in first 250 events is used for S/N analysis in pattern recognition



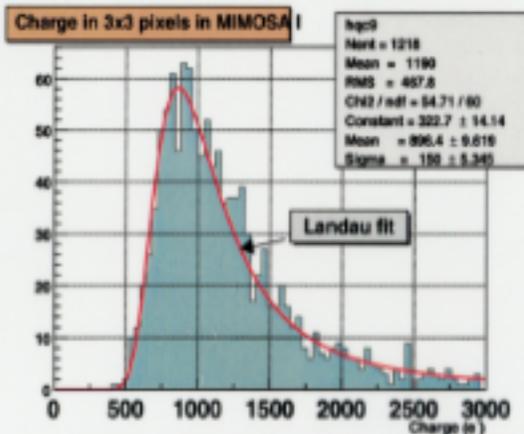
# Charge collection

After CDS only noise due to the leakage current fluctuations at the level of a few electrons remained...

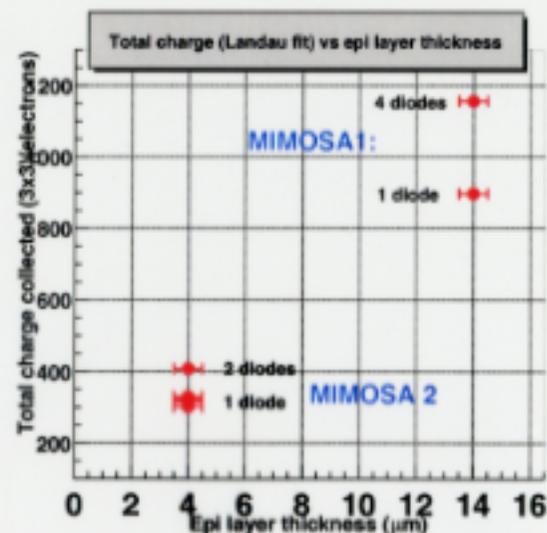
... and the signal of few hundreds of electrons was observed in accordance with the simulation



Collected charge:			
(e, $\delta \sim 1\%$ )			
	seed	3x3	pixel cluster
MIMOSA 1:	1 diode	302	896
	4 diodes	517	1155
MIMOSA2:	1 diode	110	315
	2 diodes	136	407



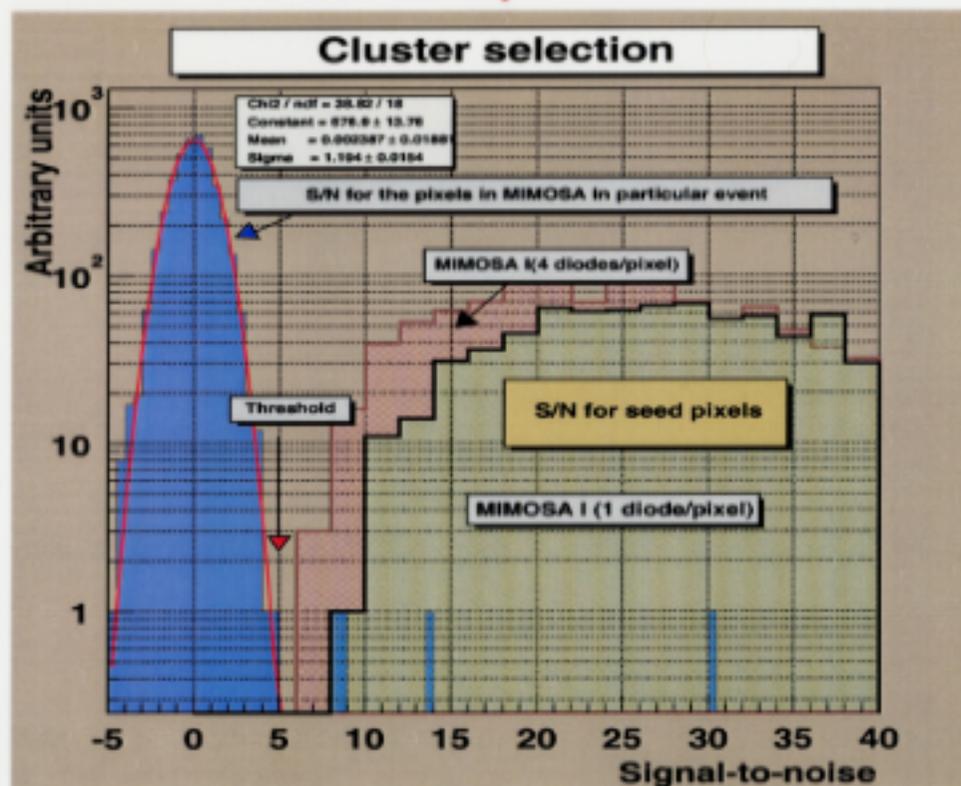
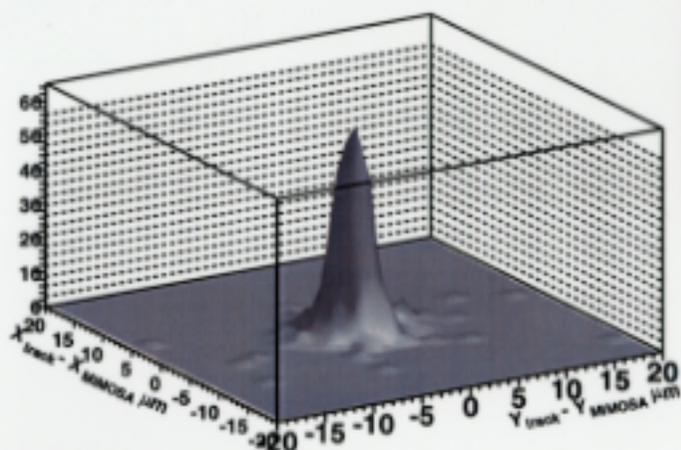
Signal-to-noise (mean):	
MIMOSA I:	1 diode 42
	4 diodes 32
MIMOSA II:	1 diode 21



# Pattern recognition and efficiency

The high S/N made the pattern recognition easy, clusters were selected using the pixels with  $S/N > 5$  as a seed

The cluster matching the track impact point was found in MIMOSA...



...with high

## Efficiency (%)

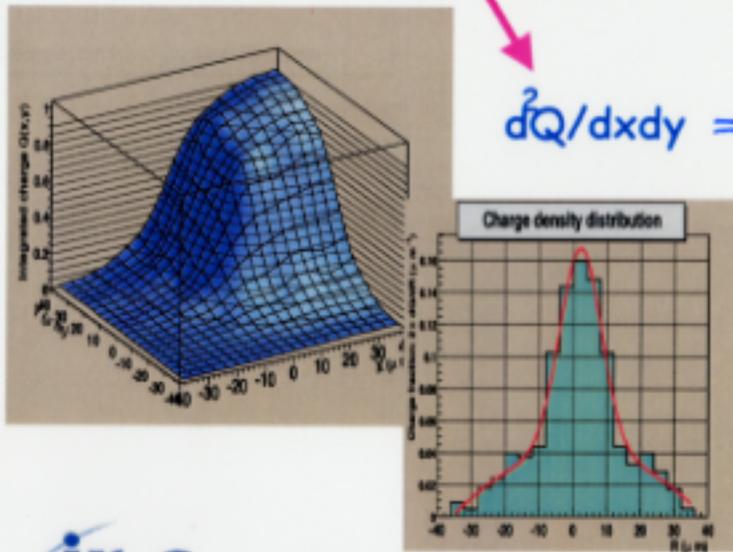
MIMOSA I: 1 diode	99.5 +/- 0.2
MIMOSA I: 4 diodes	99.2 +/- 0.2
MIMOSA II: 1 diode	98.5 +/- 0.3

# Charge distribution

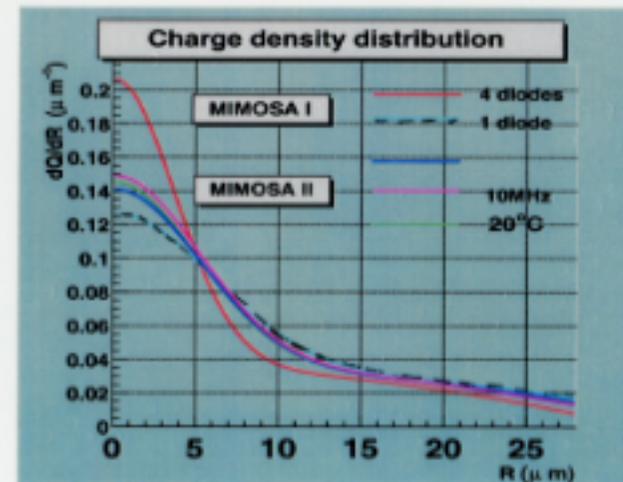
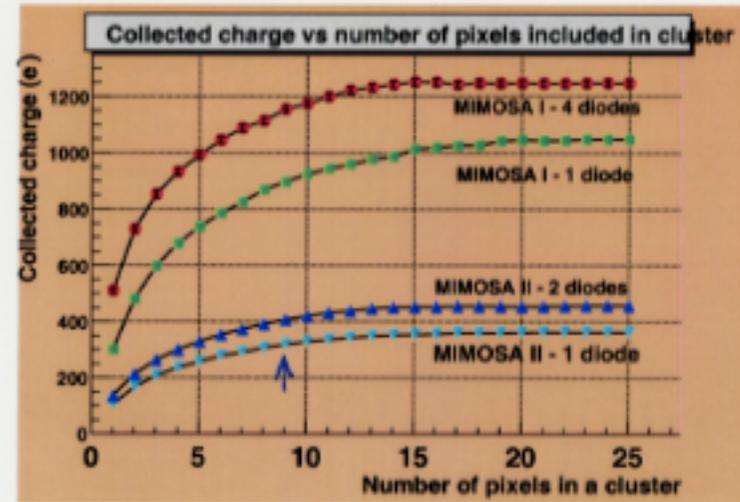
Charge is spread within a cluster of few pixels:

Charge density distribution was measured as follows:

$$Q(x_0, y_0) = \int_{-x_0}^{x_0} dy \int_{-y_0}^{y_0} q(x, y) dx$$

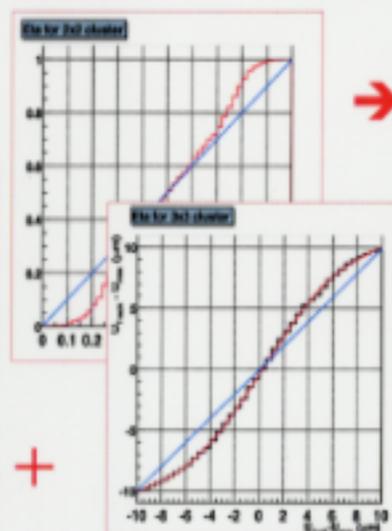
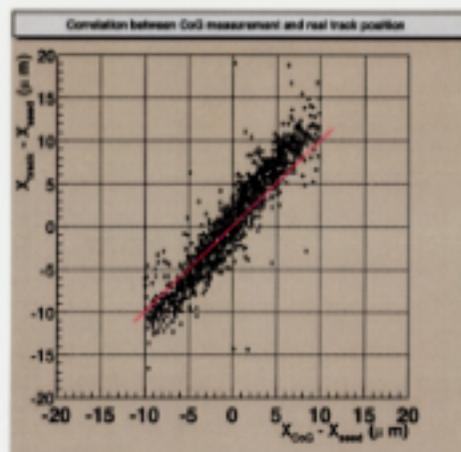


$$\frac{d^2Q}{dx dy} = q(x, y) = q(R)$$



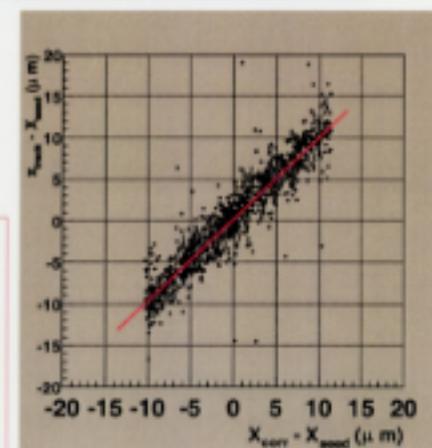
# Spatial resolution

Measure the hit position as a CoG of charge in the cluster...

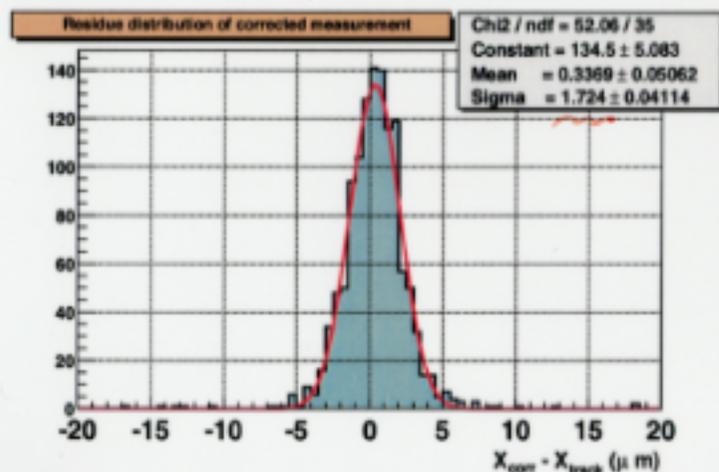


+

...with correction

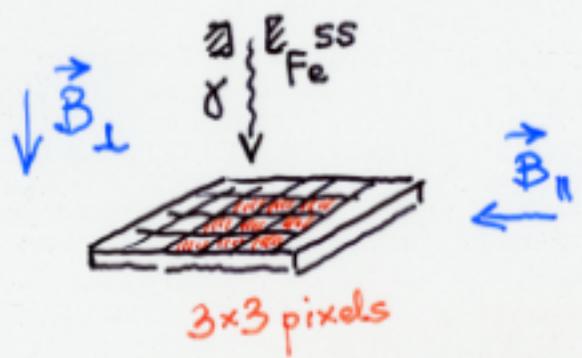
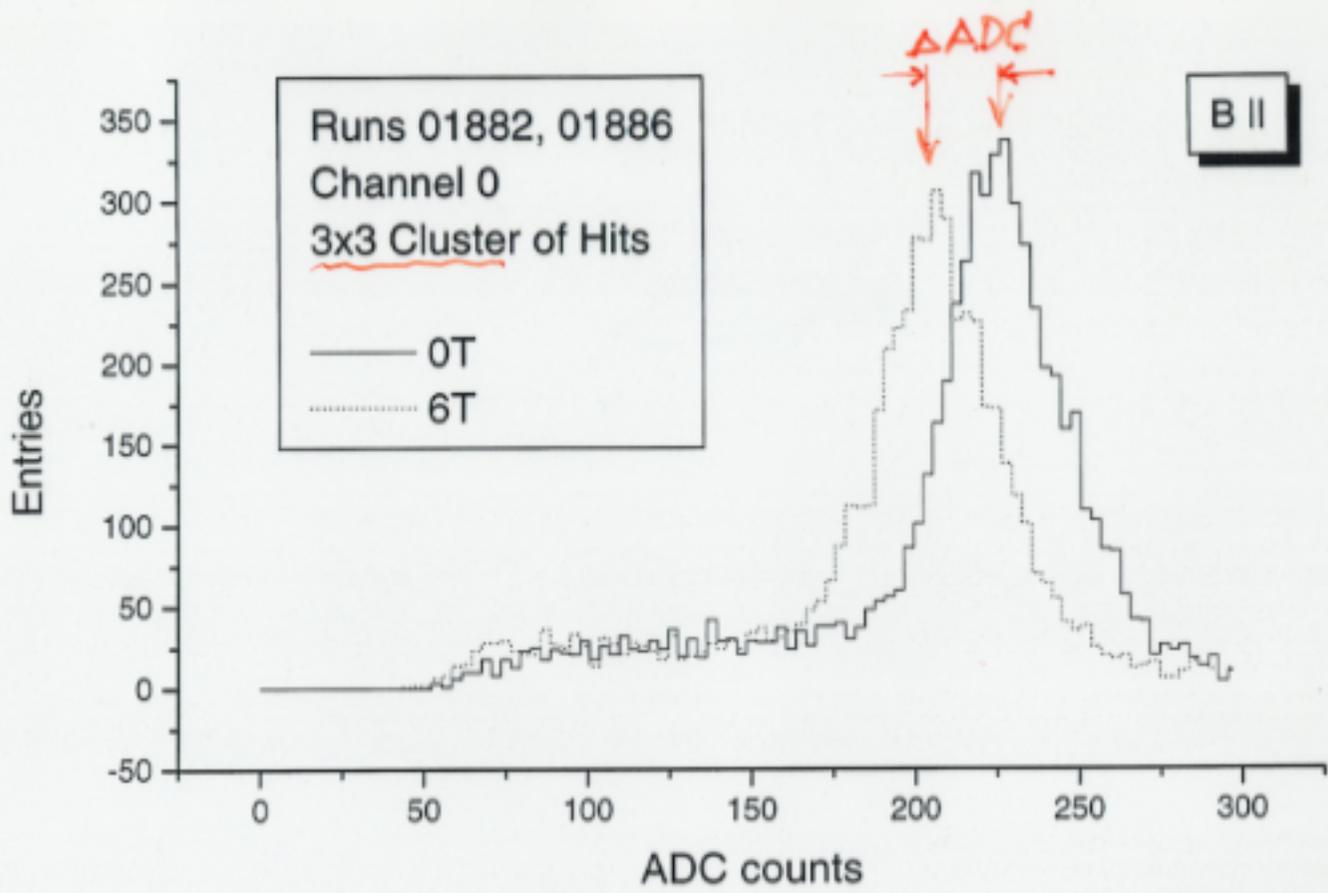


... comparing measurements with the BT prediction, and taking into account its resolution ( $1\mu\text{m}$ )



Spatial resolution ( $\mu\text{m}$ ):

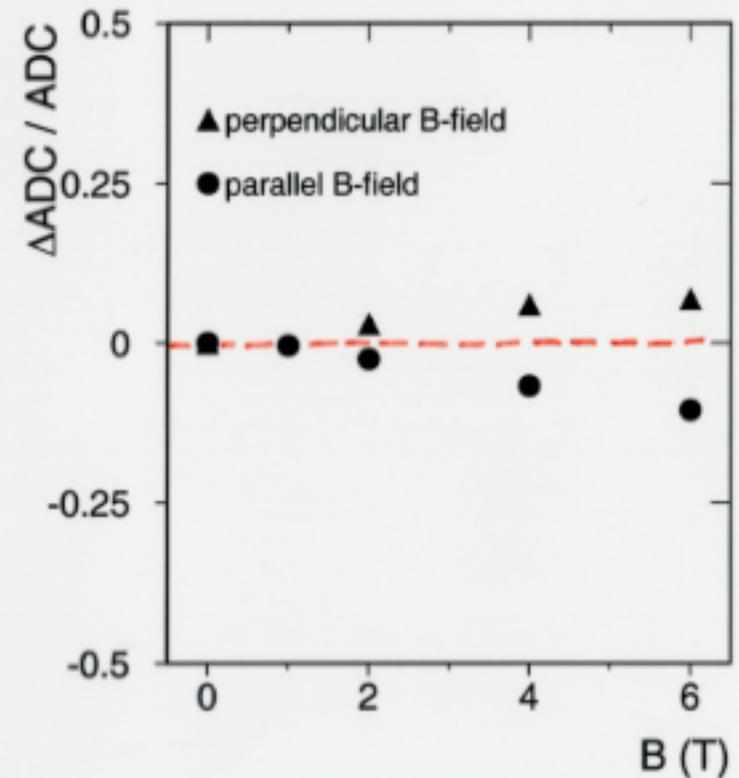
MIMOSA I: 1 diode	$1.4 \pm 0.1$
4 diodes	$2.1 \pm 0.1$
MIMOSA II: 1 diode	$2.2 \pm 0.1$



# Magnet tests

Magnet tests were performed at  
superconductive magnet of ITP (Karlsruhe)...

...only modest influence was observed



## Conclusion and prospects

- Both prototypes 0.6 and 0.35  $\mu\text{m}$  CMOS Monolithic Active Pixel Sensor work as a minimum ionising particles detector!
- Charge collection : reasonably fast ( $\sim 100\text{ns}$ ), spread limited to few pixels, good agreement between device simulation and measurements, only modest effects of magnetic field (up to 6 Tesla, both directions)
- High energy particles beam test results :  
**S/N 20-40,  $\sim 100\%$  detection efficiency, spatial resolution up to  $< 1.5\mu\text{m}$**
- Radiation hardness tests soon
- Short term future : large area ( $\sim 10\text{ cm}^2$ ) device ( $\sim$ mid 2001)
- Long term future : intelligent, high precision, ultimately thin, large area and low cost device.
- Other potential application (in addition to MIP tracking) : ?????